



# 4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38 H11A1, H11A2, H11A3, H11A4, H11A5 DC Input 6-Pin DMC-Isolator® Phototransistor Optocoupler

## Features

- High isolation 5000 VRMS
- Patented coplanar structure DMC-Isolator®
- DC input with transistor output
- Operating Temperature range - 55 °C to 110 °C
- External Creepage  $\geq 7.4\text{mm}$
- Distance Through Isolation  $\geq 0.4\text{mm}$
- Clearance Distance  $\geq 7.5\text{mm}$  (S/SL Type)
- Clearance Distance  $\geq 8.0\text{mm}$  (M Type)
- RoHS and REACH Compliance
- Halogen Free Compliance (Optional)
- MSL class 1
- Regulatory Approvals
  - ✓ UL - UL1577 (E364000)
  - ✓ VDE - EN60747-5-5(VDE0884-5)
  - ✓ CQC – GB4943.1, GB8898 (14001105802)
  - ✓ IEC62368 (FI/41119)

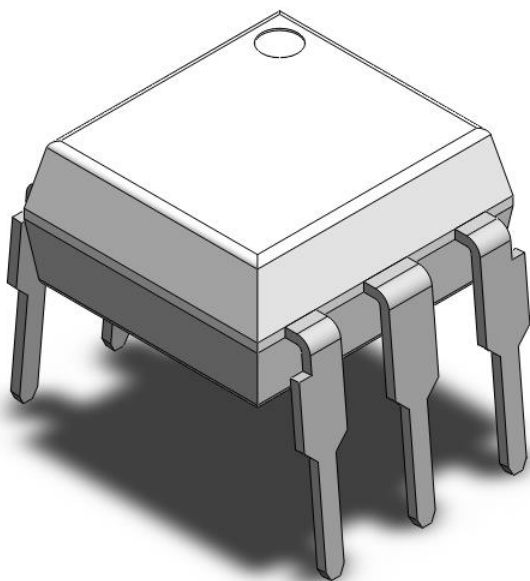
## Description

The 4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38, H11A1, H11A2, H11A3, H11A4, H11A5 series consist of a photo transistor optically coupled to an Infrared-emitting diode in a 6-lead DIP DMC-Isolator® package with different lead forming options.

## Applications

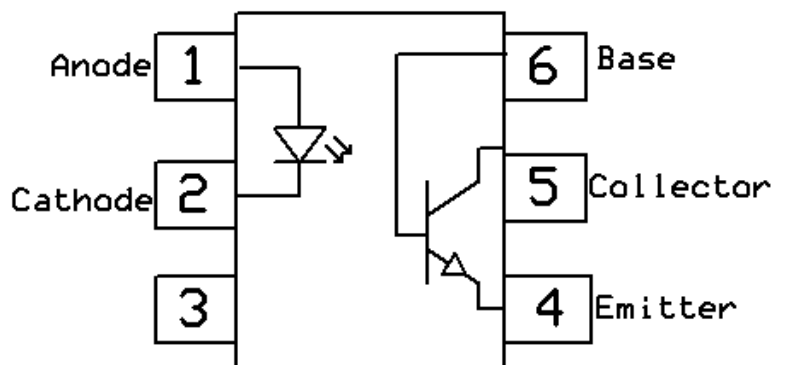
- Microprocessor system interface
- Computer peripheral interface
- Switch mode power supplies

## Package Outline



Note: Different bending options available. See package dimension.

## Schematic





**Absolute Maximum Ratings**  $T_A = 25^{\circ}\text{C}$ , unless otherwise specified

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Ratings	Units	Notes
V <sub>ISO</sub>	Isolation voltage (AC, 1 minute, 40 ~ 60% R.H.)	5000	V <sub>RMS</sub>	
T <sub>OPR</sub>	Operating temperature	-55 ~ +110	°C	
T <sub>STG</sub>	Storage temperature	-55 ~ +150	°C	
T <sub>SOL</sub>	Soldering temperature (For 10 seconds)	260	°C	
<b>Emitter</b>				
I <sub>F</sub>	Forward current	60	mA	
I <sub>F(TRANS)</sub>	Peak transient current (≤1μs P.W,300pps)	1	A	
V <sub>R</sub>	Reverse voltage	6	V	
P <sub>D</sub>	Power dissipation	100	mW	
<b>Detector</b>				
P <sub>D</sub>	Power dissipation	150	mW	
B <sub>VCEO</sub>	Collector-Emitter Breakdown Voltage	80	V	
B <sub>VCBO</sub>	Collector-Base Breakdown Voltage	80	V	
B <sub>VECO</sub>	Emitter-Collector Breakdown Voltage	7	V	
B <sub>VEBO</sub>	Emitter-Base Breakdown Voltage	7	V	



Electrical Characteristics  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$V_F$	Forward voltage	$I_F = 10\text{mA}$		1.24	1.4	V	
$I_R$	Reverse Current	$V_R = 6\text{V}$	-	-	5	$\mu\text{A}$	
$C_{IN}$	Input Capacitance	$f = 1\text{MHz}$	-	45	-	pF	

Detector Characteristics

Symbol	Parameters		Test Conditions	Min	Typ	Max	Units	Notes
$B_{V_{CEO}}$	Collector-Emitter Breakdown		$I_C = 0.1\text{mA}$	80	-	-	V	
$B_{V_{ECO}}$	Emitter-Collector Breakdown		$I_E = 0.1\text{mA}$	7	-	-	V	
$B_{V_{CBO}}$	Collector-Base Breakdown		$I_C = 0.1\text{mA}$	80	-	-	V	
$B_{V_{EBO}}$	Emitter-Base Breakdown		$I_E = 0.1\text{mA}$	7	-	-	V	
$I_{CEO}$	Collector-Emitter	4N25,4N26,4N27,4N28	$V_{CE} = 10\text{V}, I_F = 0\text{mA}$	-	-	50	nA	
	Dark Current	H11A1,A2,A3,A4,A5						
		4N35,4N36,4N37,4N38						
$I_{CBO}$	Collector-Base Dark Current		$V_{CB} = 10\text{V}, I_F = 0\text{mA}$	-	-	20	nA	



**Electrical Characteristics**  $T_A = 25^\circ\text{C}$ , unless otherwise specified (Continued)

**Transfer Characteristics**

Symbol	Parameters		Test Conditions	Min	Typ	Max	Units	Notes
CTR	Current Transfer Ratio	4N35, 4N36, 4N37	$I_F = 10\text{mA}, V_{CE} = 10\text{V}$	100	-	-	%	
		4N25, 4N26, 4N38, H11A2, H11A3		20	-	-		
		4N27, 4N28, H11A4		10	-	-		
		H11A1		50	-	-		
		H11A5		30	-	-		
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	4N25, 4N26, 4N27, 4N28	$I_F = 50\text{mA}, I_C = 2\text{mA}$	-	-	0.5	V	
		4N35, 4N36, 4N37	$I_F = 10\text{mA}, I_C = 0.5\text{mA}$	-	-	0.3		
	H11A1, H11A2, H11A3, H11A4, H11A5	-		-	0.4			
	4N38	$I_F = 20\text{mA}, I_C = 4\text{mA}$	-	-	1.0			
$R_{IO}$	Isolation Resistance		$V_{IO} = 500\text{V}_{DC}$	$1 \times 10^{11}$			$\Omega$	
$C_{IO}$	Isolation Capacitance		$f = 1\text{MHz}$		0.25		pF	

**Switching Characteristics**

Symbol	Parameters		Test Conditions	Min	Typ	Max	Units	Notes
$t_{on}$	Turn On Time	4N25, 4N26, 4N27, 4N28 H11A1, A2, A3, A4, A5	$I_F = 10\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$	-	4.3	9.8	$\mu\text{s}$	
		4N35, 4N36, 4N37, 4N38	$I_C = 2\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$	-	9.8	11.5		
$t_{off}$	Turn Off Time	4N25, 4N26, 4N27, 4N28 H11A1, A2, A3, A4, A5	$I_F = 10\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$	-	3.9	9.8	$\mu\text{s}$	
		4N35, 4N36, 4N37, 4N38	$I_C = 2\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$	-	6.9	11.5		



Typical Characteristic Curves  $T_A = 25^\circ\text{C}$ , unless otherwise specified

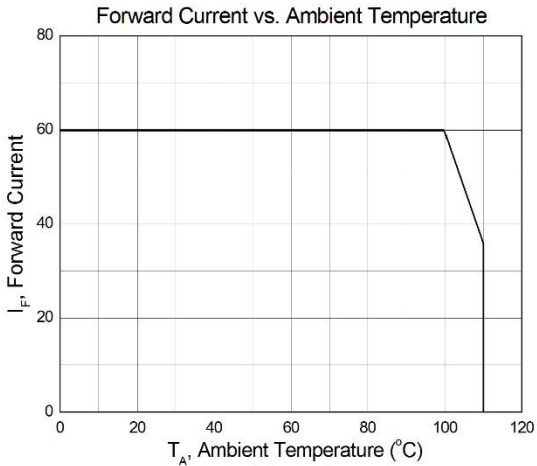


Figure 1

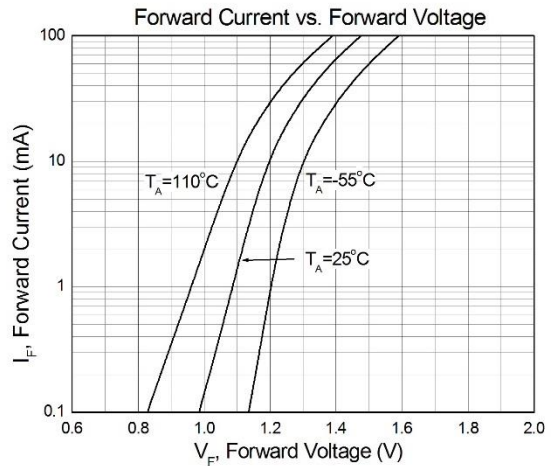


Figure 2

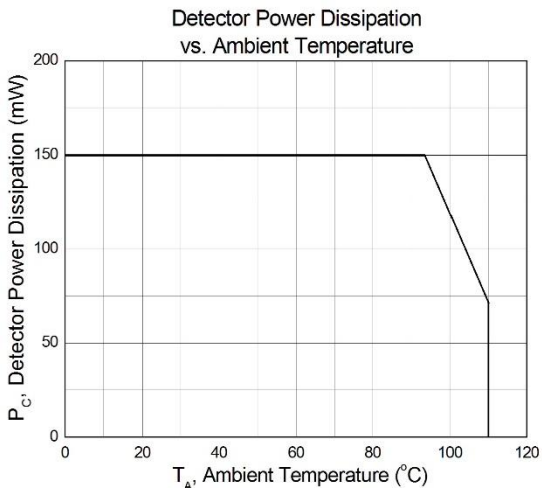


Figure 3

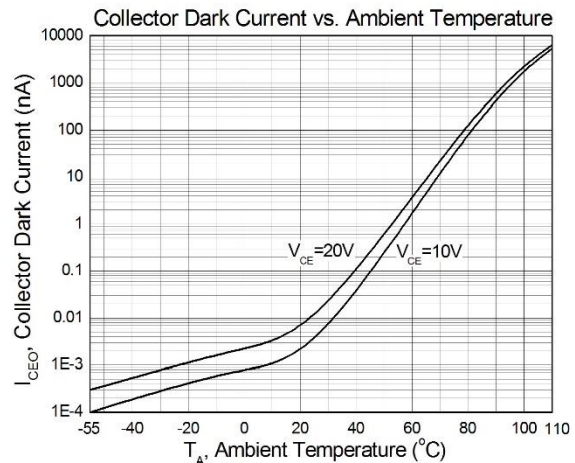


Figure 4

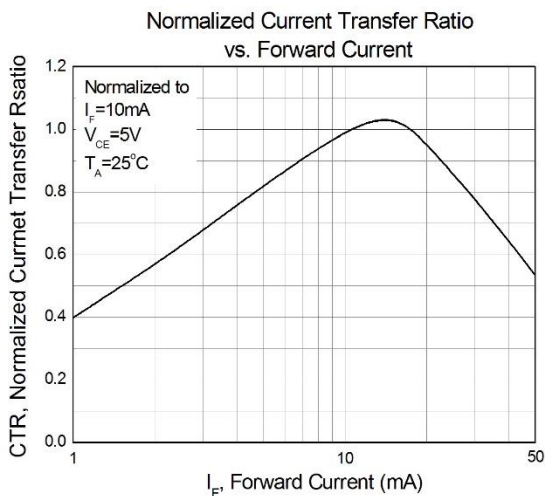


Figure 5

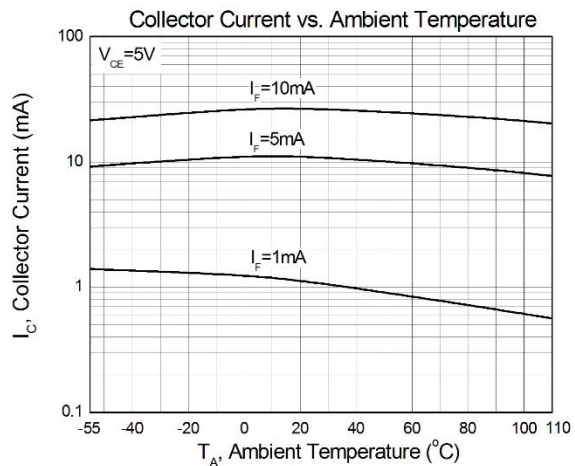


Figure 6



Typical Characteristic Curves  $T_A = 25^\circ\text{C}$ , unless otherwise specified (Continued)

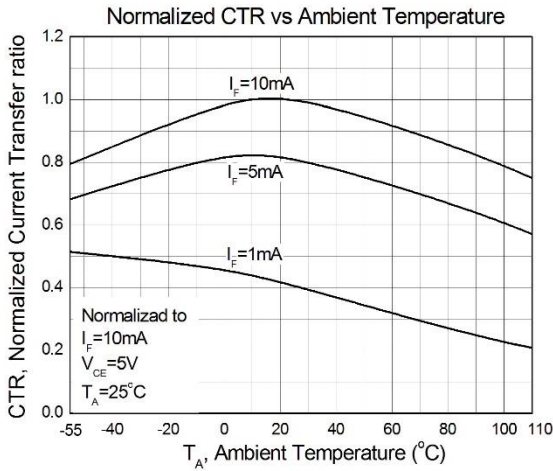


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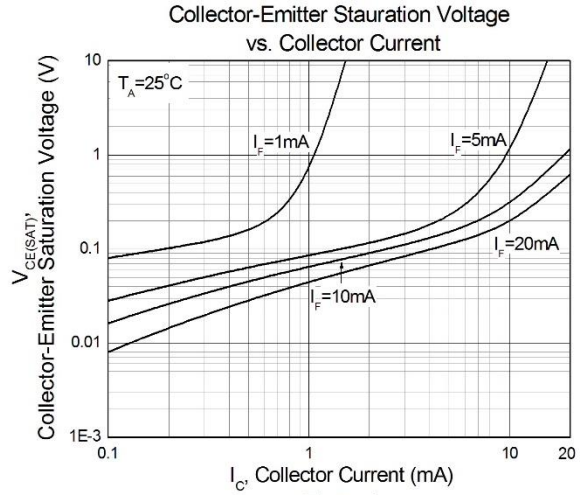


Figure 8

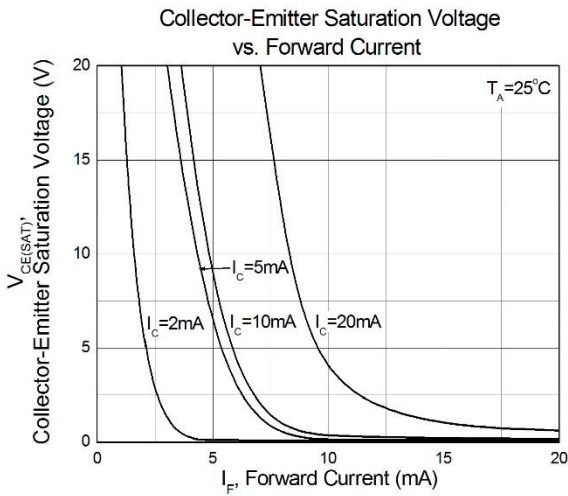


Figure 9

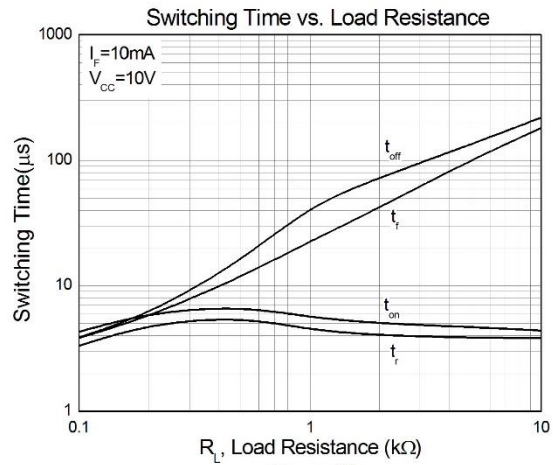


Figure 10

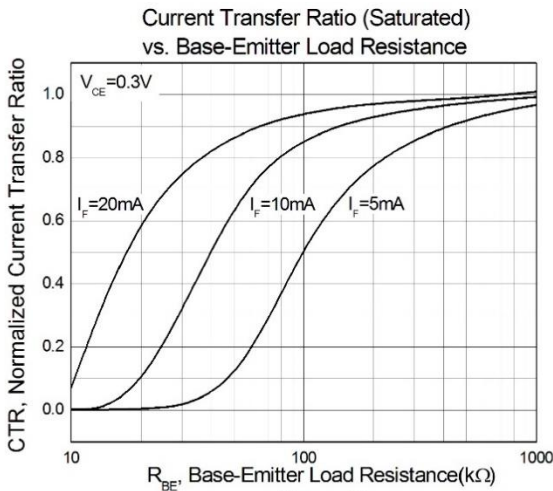


Figure 11

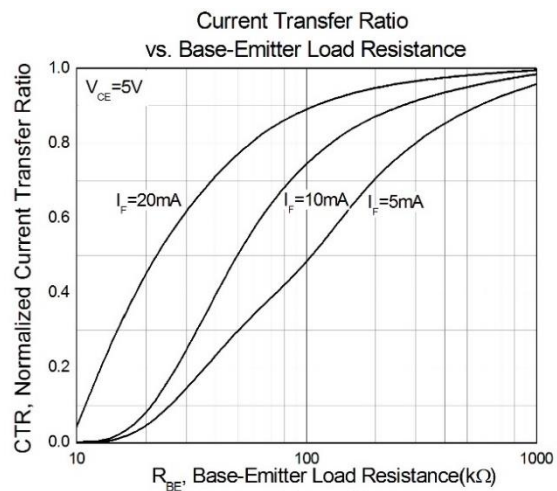


Figure 12



# 4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38 H11A1, H11A2, H11A3, H11A4, H11A5 DC Input 6-Pin DMC-Isolator® Phototransistor Optocoupler

## Typical Characteristic Curves $T_A = 25^\circ\text{C}$ , unless otherwise specified (Continued)

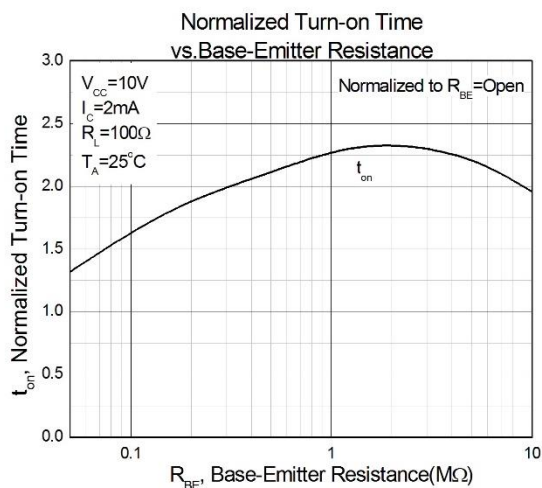


Figure 13

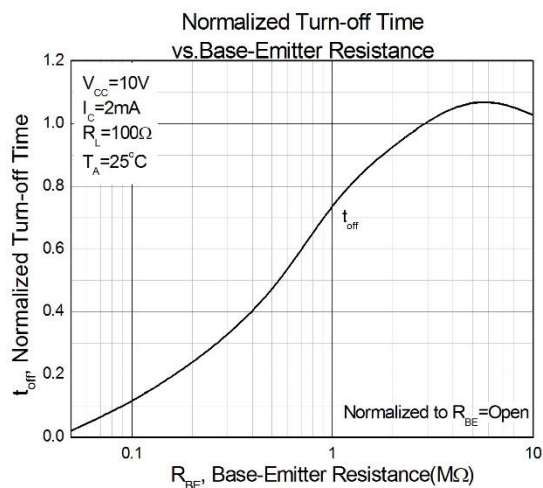
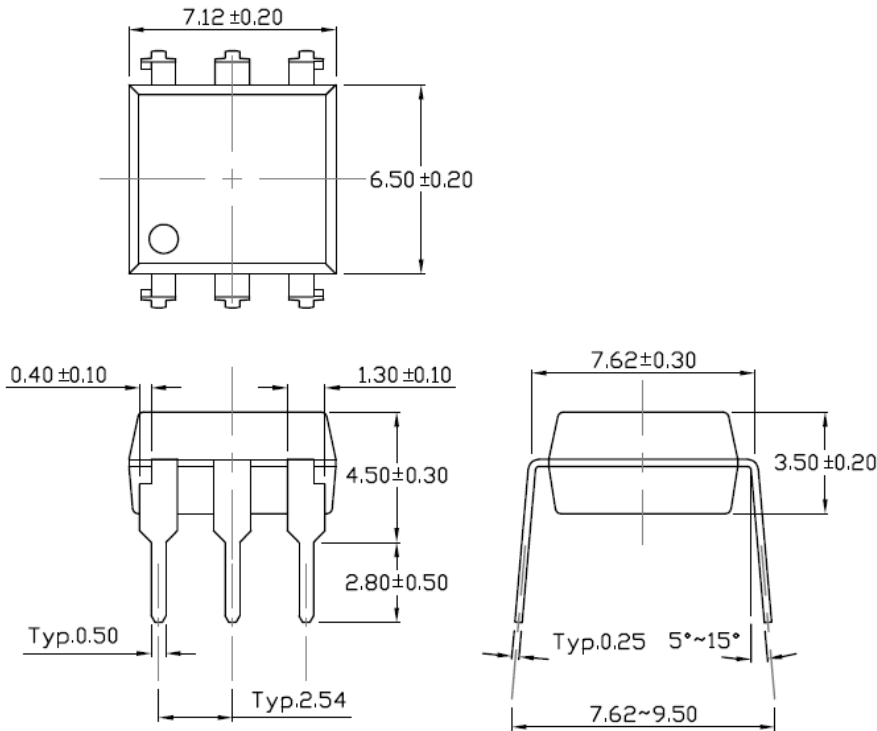


Figure 14



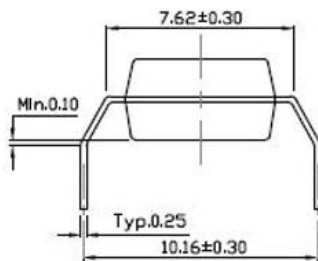
**Package Dimension** *Dimensions in mm unless otherwise stated*

**Standard DIP – Through Hole**

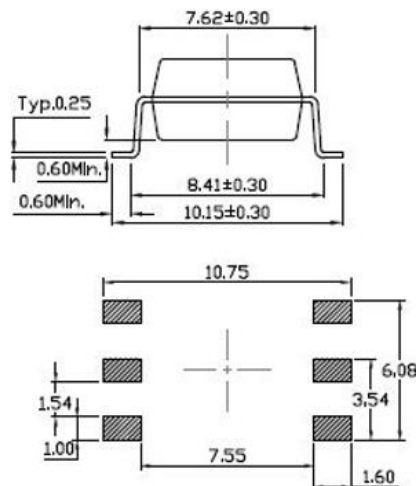


**Forming Option**

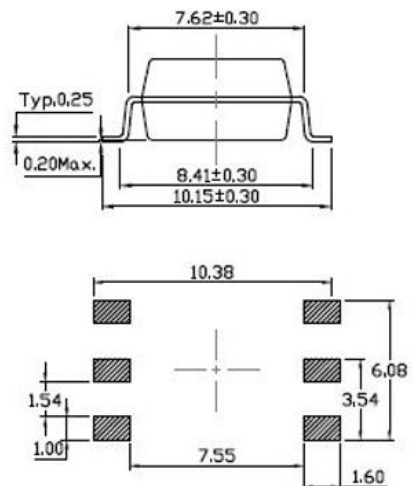
**M Type**



**S Type**



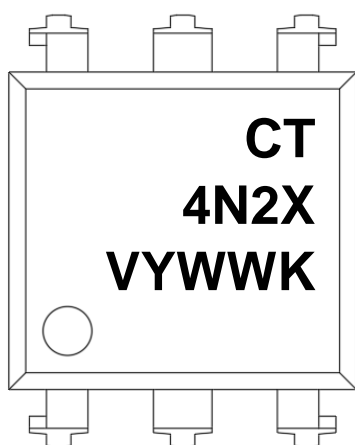
**SL Type**





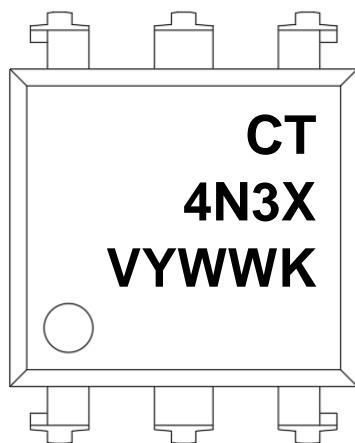


### Marking Information



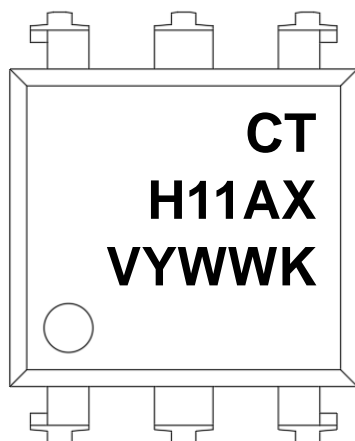
**Note:**

- CT : Denotes "CT Micro"
- 4N2X : Part Number (X=5,6,7 or 8)
- V : VDE Safety Mark Option (Blank or V)
- Y : One Digit Year Code
- WW : Two Digit Work Week
- K : Manufacturing Code



**Note:**

- CT : Denotes "CT Micro"
- 4N3X : Part Number (X=5,6,7 or 8)
- V : VDE Safety Mark Option (Blank or V)
- Y : One Digit Year Code
- WW : Two Digit Work Week
- K : Manufacturing Code



**Note:**

- CT : Denotes "CT Micro"
- H11AX: Part Number (X=1,2,3,4 or 5)
- V : VDE Safety Mark Option (Blank or V)
- Y : One Digit Year Code
- WW : Two Digit Work Week
- K : Manufacturing Code



## Ordering Information

### 4N2X(V)(Y)(Z)-G, 4N3X(V)(Y)(Z)-G

- X = Part Number (X=5,6,7 or 8)
- V = VDE Safety Mark Option (Blank or V)
- Y = Lead Form Option (Blank, M, S or SL)
- Z = Tape and Reel Option (Blank, T1 or T2)
- G = Material Option (G: Halogen Free, Blank: Non-Halogen Free)

### H11AX(V)(Y)(Z)-G

- X = Part Number (1,2,3,4 or 5)
- V = VDE Safety Mark Option (Blank or V)
- Y = Lead Form Option (Blank, M, S or SL)
- Z = Tape and Reel Option (Blank, T1 or T2)
- G = Material Option (G: Halogen Free, Blank: Non-Halogen Free)

<b>Option</b>	<b>Description</b>	<b>Quantity</b>
None	Standard 6 Pin Dip	50Units/Tube
M	Wide Lead Forming	50Units/Tube
S(T1)	Surface Mount Lead Forming – With Option A Taping	1000 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option B Taping	1000 Units/Reel
SL(T1)	Surface Mount Lead Forming (Low Profile) – With Option A Taping	1000 Units/Reel
SL(T2)	Surface Mount Lead Forming (Low Profile) – With Option B Taping	1000 Units/Reel



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4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38

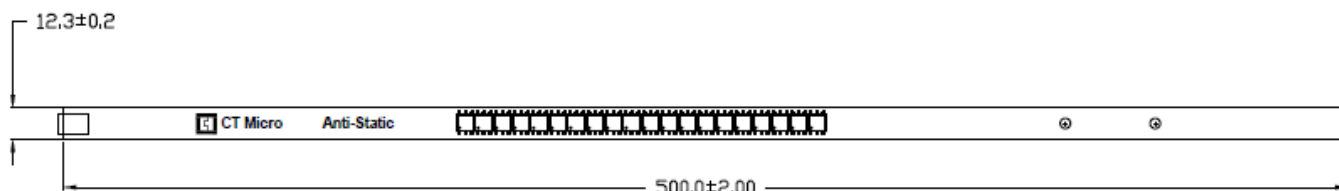
H11A1, H11A2, H11A3, H11A4, H11A5

DC Input 6-Pin DMC-Isolator®

Phototransistor Optocoupler

### Carrier Specifications *Dimensions in mm unless otherwise stated*

#### Tube Option Standard DIP

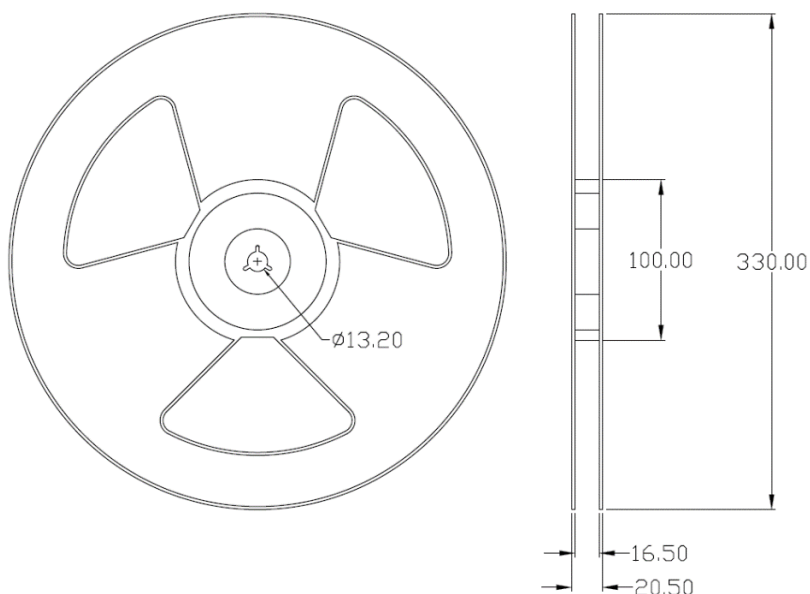


#### Tube Option M Type



### Reel Dimension *All dimensions are in mm, unless otherwise stated*

#### Option S(T1/T2) & SL(T1/T2)

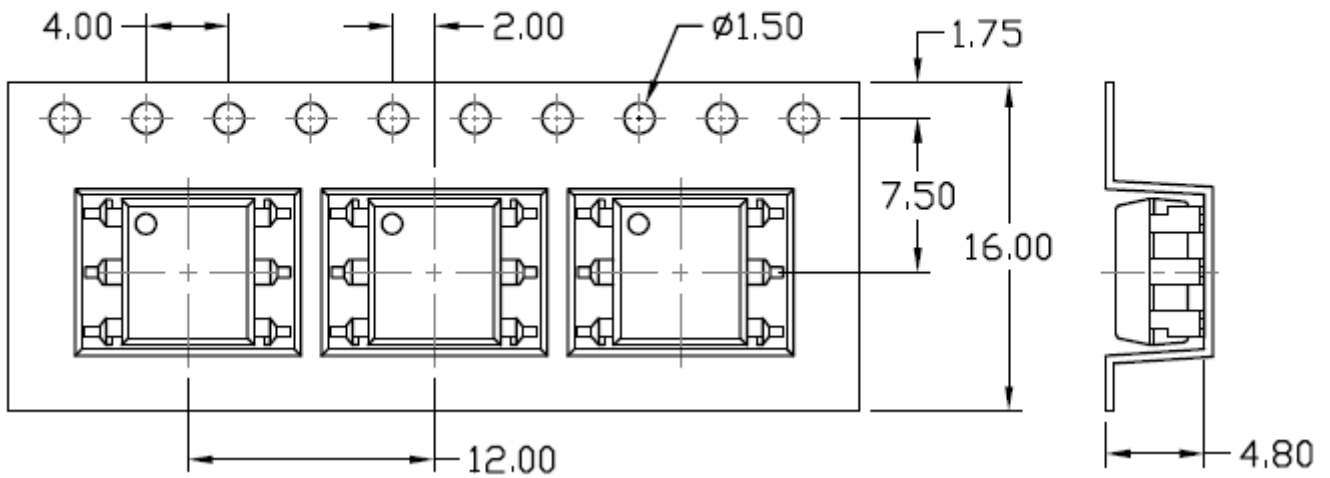




**Carrier Tape Specifications** *Dimensions in mm unless otherwise stated*

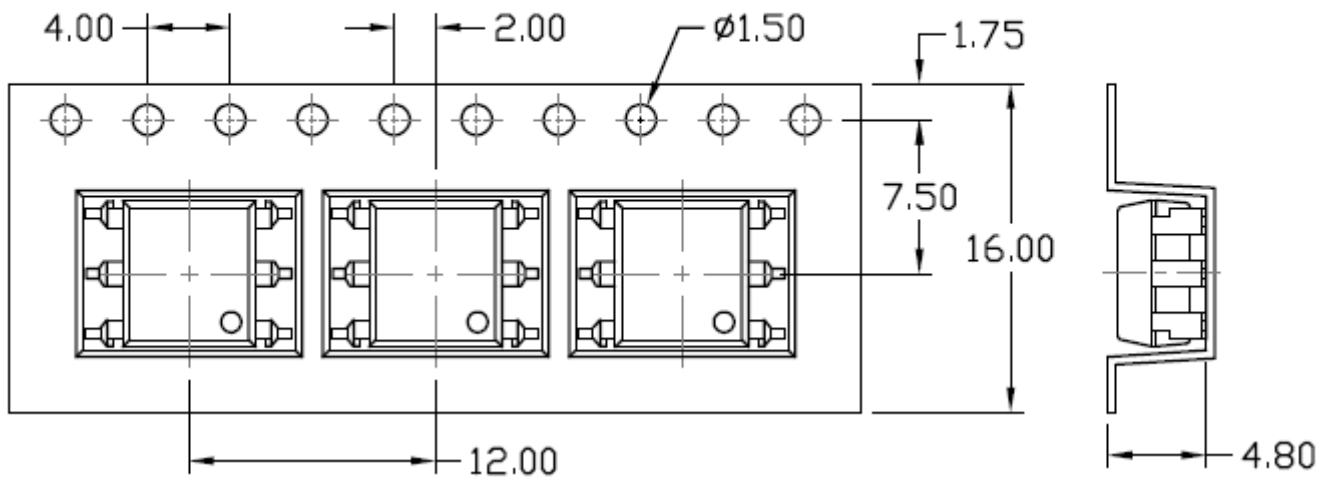
**Option S (T1) & SL (T1)**

Input Direction  
→



**Option S (T2) & SL (T2)**

Input Direction  
→





### Solderability spec (follow the JEDEC standard JESD22-B102)

Reflow Soldering: Immersed surface, other than the end of pin as cut-surface, must be covered by solder.

Solder-Bath: More than 95% of the electrode must be covered with solder.

### Wave soldering (follow the JEDEC standard JESD22-A111)

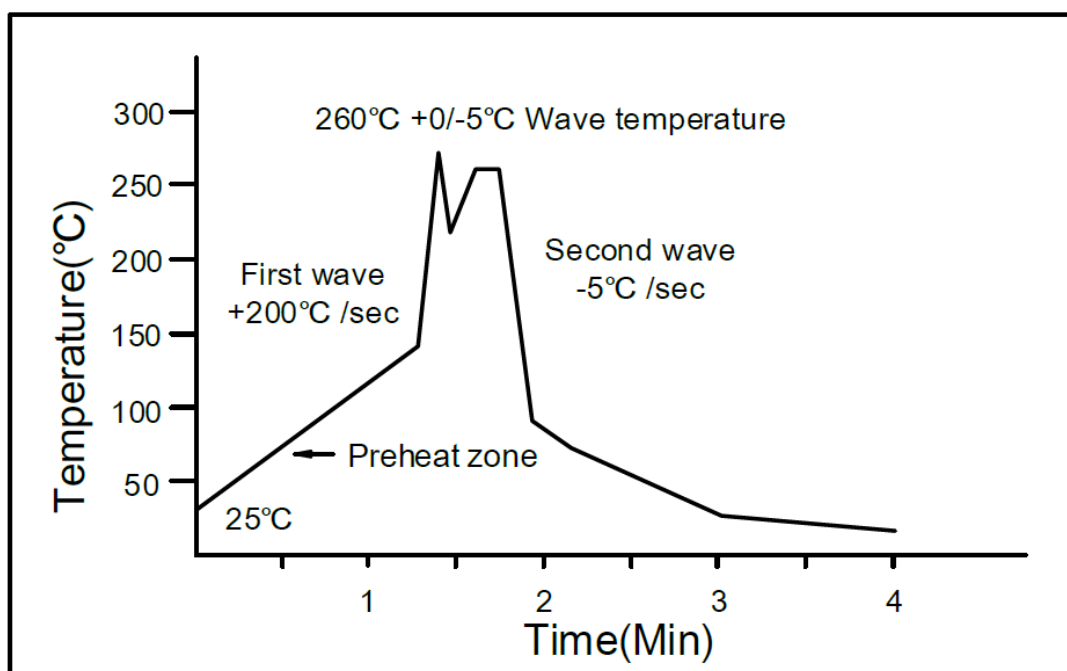
One time soldering is recommended within the condition of temperature.

Temperature:  $260 \pm 5^\circ\text{C}$ .

Time: 10 sec.

Preheat temperature: 25 to  $140^\circ\text{C}$ .

Preheat time: 30 to 80 sec.



### Iron Soldering (follow the standard MIL-STD 202G, Method 210F)

Allow single lead soldering in every single process.

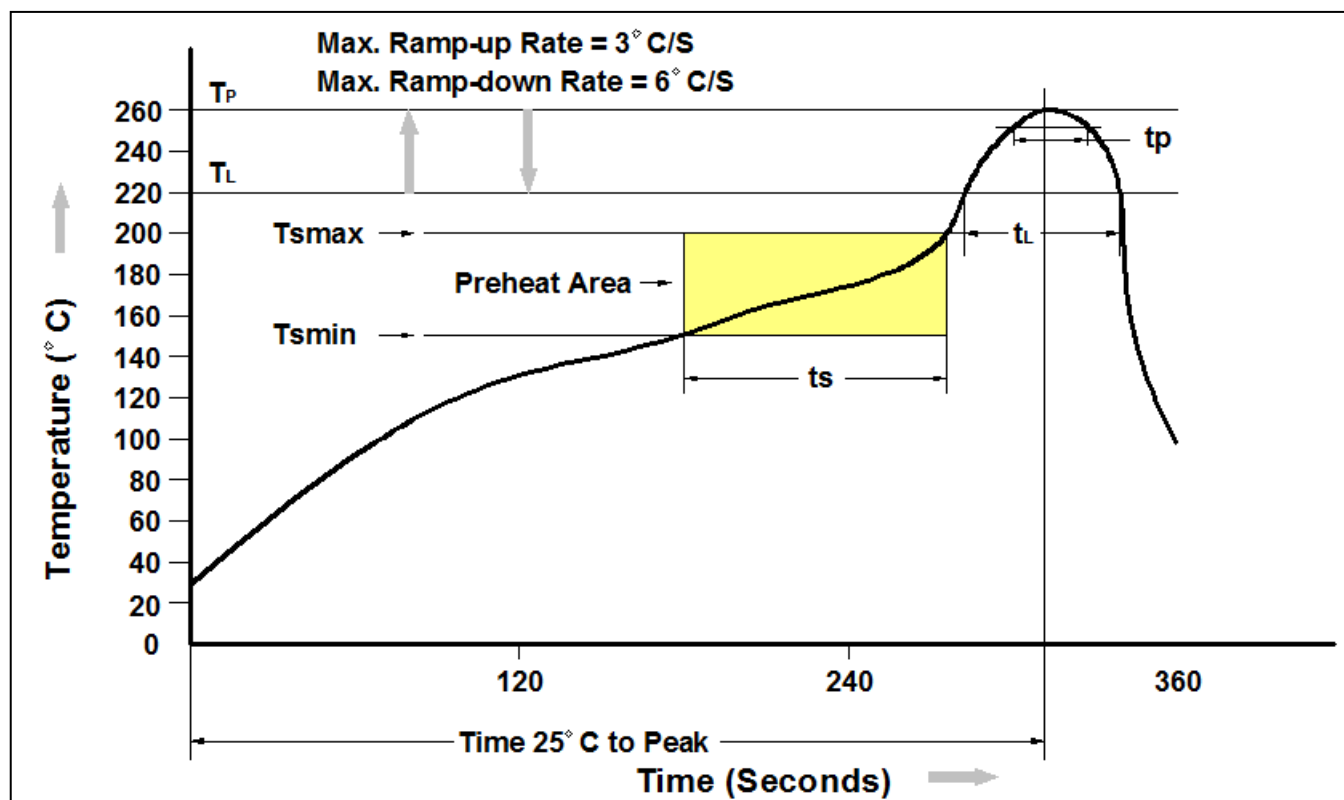
One time soldering is recommended.

Temperature:  $350 \pm 10^\circ\text{C}$

Time: 5 sec max.



Reflow Profile (follow the JEDEC standard J-STD-020)



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T <sub>smin</sub> )	150°C
Temperature Max. (T <sub>smax</sub> )	200°C
Time (t <sub>s</sub> ) from (T <sub>smin</sub> to T <sub>smax</sub> )	60-120 seconds
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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H11A1, H11A2, H11A3, H11A4, H11A5  
DC Input 6-Pin DMC-Isolator®  
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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.*